

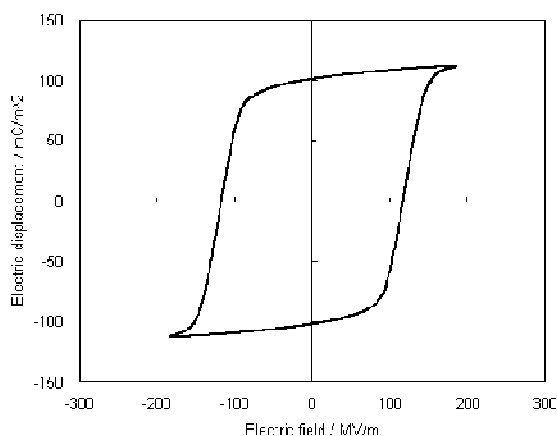
## Ferroelectric and piezoelectric properties of newly synthesized vinylidene fluoride telomer with $C_nF_{2n+1}$ group

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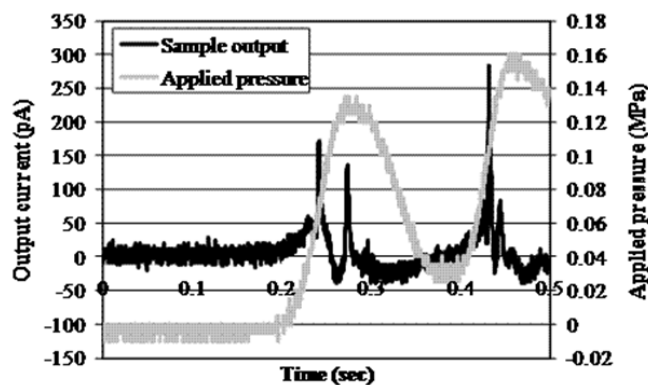
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Organic ferroelectric thin films have been well studied in recent years due to their applicability to transducers, sensors, actuators and memory devices. Poly vinylidene fluoride (PVDF) and its copolymer with trifluoroethylene, [P(VDF/TrFE)] are well known to be ferroelectric polymers. However, it is difficult to fabricate the highly oriented polymer films with high crystallinity. Here, we focused on newly synthesized vinylidene fluoride (VDF) telomer [ $C_6F_{13}(CH_2CF_2)_{23}I$ ] with low-molecular-weight. Ferroelectric and piezoelectric properties of its highly oriented thin film deposited by vacuum evaporation method were investigated. **Figure 1** shows the  $D-E$  hysteresis characteristic of Al/VDF/Al capacitor. The VDF telomer films showed clear hysteresis loop, and the corresponding value of remanent polarization ( $P_r$ ) was  $100 \text{ mC/m}^2$ . The value of  $P_r$  was tend to be smaller than that of  $CF_3(CH_2CF_2)_{17}I$  ( $130 \text{ mC/m}^2$ )<sup>[1]</sup>. This result may indicate that the  $R_F$  ( $C_nF_{2n+1}$ ) group is invalid for  $P_r$ . We also measured the piezoelectric response of the evaporated film of VDF telomer (**Fig. 2**). The piezoelectric coefficient  $d_{33}$  calculated from the relationship between the applied stress rate and output current was estimated to be  $268 \text{ pC/N}$ , which is higher than that of  $CF_3(CH_2CF_2)_{13.4}C_2H_5$  ( $181 \text{ pC/N}$ )<sup>[2]</sup>. These results suggest depending on the difference of the stiffness properties arising from the  $R_F$  groups.

1. K. Noda, et al., J. App. Phys. 2003, 93, 28866-28870.
2. K. Takashima, et al., J. Robotics Soc. Jpn. 2008, 26, 711-717.



**Figure 1**  $D-E$  hysteresis curves observed for the 300-nm-thick  $C_6F_{13}(CH_2CF_2)_{23}I$  telomer film.



**Figure 2** Piezoelectric response (black line) of  $C_6F_{13}(CH_2CF_2)_{23}I$  telomer film with applying cyclic pressure stress (gray line).